

PLASMA PROCESSING APPARATUS AND ADSORPTION CONTROL METHOD

ABSTRACT

A plasma processing apparatus includes a plasma
5 processing chamber, a base, an electrostatic chuck, a first
electrode, a second electrode, a power source, and a
controller. The base is disposed in the plasma processing
chamber. The electrostatic chuck is disposed over the base
and includes a substrate support surface and a ring support
10 surface. The first electrode is disposed under the
substrate support surface in the electrostatic chuck and
adsorbs a substrate using an electrostatic force. The
second electrode is disposed in the electrostatic chuck to
surround periphery of the first electrode. The power
15 source is electrically connected to the second electrode.
The controller executes a process including a step of
acquiring a voltage of a ring assembly disposed on the ring
support surface and a step of controlling an output voltage
of the power source according to a value of the acquired
20 voltage.

Figure 3